IN THE CLAIMS:

Please cancel Claims 1 through 5, 7 and 11 through 15 without prejudice and without dedication or abandonment of the subject matter thereof..

Please and amend Claims 6, 8 and 16 as follows:

6. (Amended) A method for forming a nitride read only memory, the method comprising:

providing a P-type semiconductor substrate;

forming a stacked oxide-nitride-oxide layer on said P-type semiconductor substrate;

forming and defining a plurality of photoresister layers on said stacked oxide-nitride-oxide layer to expose a portion of said stacked oxide-nitride-oxide layer;

performing an etching process by way of using said plurality of photoresister layers as a plurality of etching masks to etch said stacked oxide-nitride-oxide layer and form a plurality of read only memory cells;

performing a pocketed ion-implantation with an indium ion at least one time by way of using said plurality of photoresister layers as a plurality of ion-implanting masks to form a plurality of pocket dopant regions having said indium ion in said P-type semiconductor substrate;

performing afterward an N-type ion-implanting process by way of using said plurality of photoresister layers as said ion-implanting masks to form a plurality of N-type ion-implanting regions in said P-type semiconductor substrate between said plurality of photoresist layers; and

removing said plurality of photoresist layers to form said read only memory.

8. (Amended) The method according to claim 6, wherein the method for forming said stacked oxide-nitride-oxide layer comprises a depositing process.

16. (Amended) A method for forming a nitride read only memory, the method comprising:

providing a P-type semiconductor substrate;

forming an oxide-nitride-oxide layer on said P-type semiconductor substrate;

forming and defining a plurality of photoresister layers on said oxide-nitride-oxide layer to expose a portion of said oxide-nitride-oxide layer;

performing an etching process by way of using said plurality of photoresister layers as a plurality of etching masks to etch said oxide-nitride-oxide layer and form a plurality of read only memory cells;

performing an N-type ion-implanting process by way of using said plurality of photoresister layers as an ion-implanting masks to form a plurality of N-type ion-implanting regions in said P-type semiconductor substrate between said plurality of read only memory cells;

performing a pocketed ion-implantation with an indium ion at least two time by way of using said plurality of photoresister layers as said plurality of ion-implanting masks to form a plurality of pocket dopant regions having said indium ion beside said P-type semiconductor substrate under said plurality of memory cells; and

removing said plurality of photoresist layers to form said nitride read only memory.